

# THE EXTREME ULTRAVIOLET SOURCE DEVELOPED AT CEA SACLAY IN THE FRAME OF THE FRENCH NATIONAL PROJECT PREUVE

O. Sublemontier, M. Bouchon, M. Bougeard, E. Caprin,  
T. Ceccotti, A. Fillon, D. Guyader, L. Lederoff, M. Segers,  
M. Schmidt and D. Normand

*CEA/DSM/DRECAM/SPAM, CE Saclay, 91191 Gif sur Yvette, FRANCE*

P. Cormont, V. Le Flanchec, J.M. Weulersse and M. Neu  
*CEA/DCC/DPE/SLCS, CE SACLAY, Gif sur Yvette, FRANCE*

C. Simon-Boisson, J.L. Ayrat and J.M. Barbiche  
*THOMSON TCL, FRANCE*

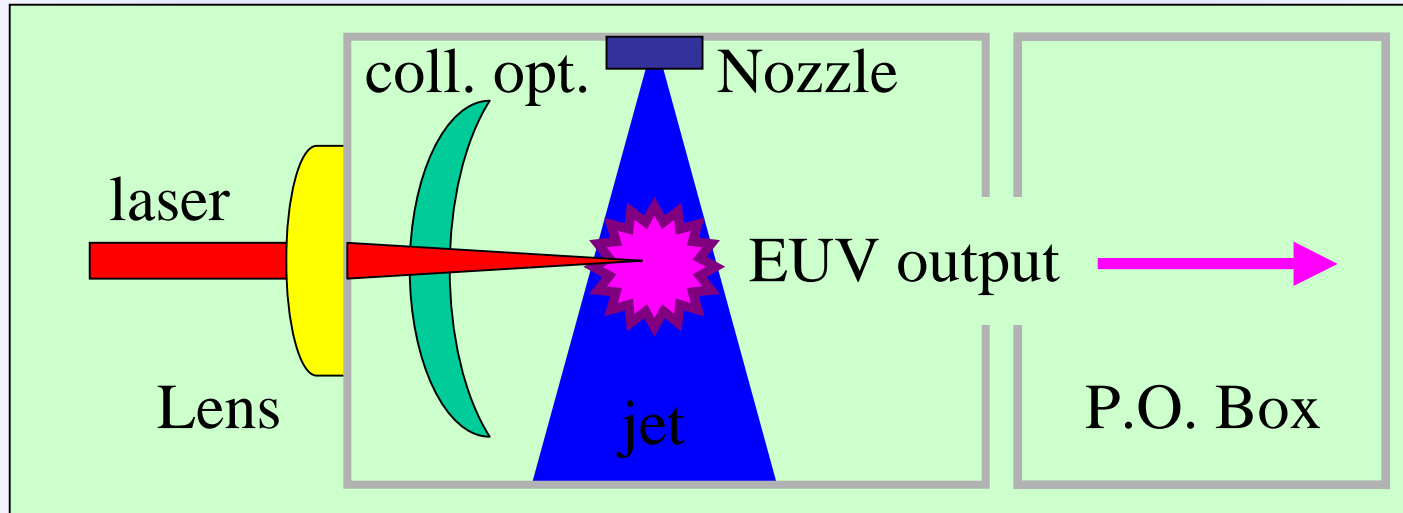
# Modular design of the EUV source

- Mastered development costs
- Increased reliability by the redundancy of pumping laser sources
- Facilitated maintenance
- Easy extrapolation towards higher powers if required ( $\alpha$ -tool,  $\beta$ -tool, commercial tool)

Solution based on high repetition rate lasers is preferred for economic, technical and industrial reasons

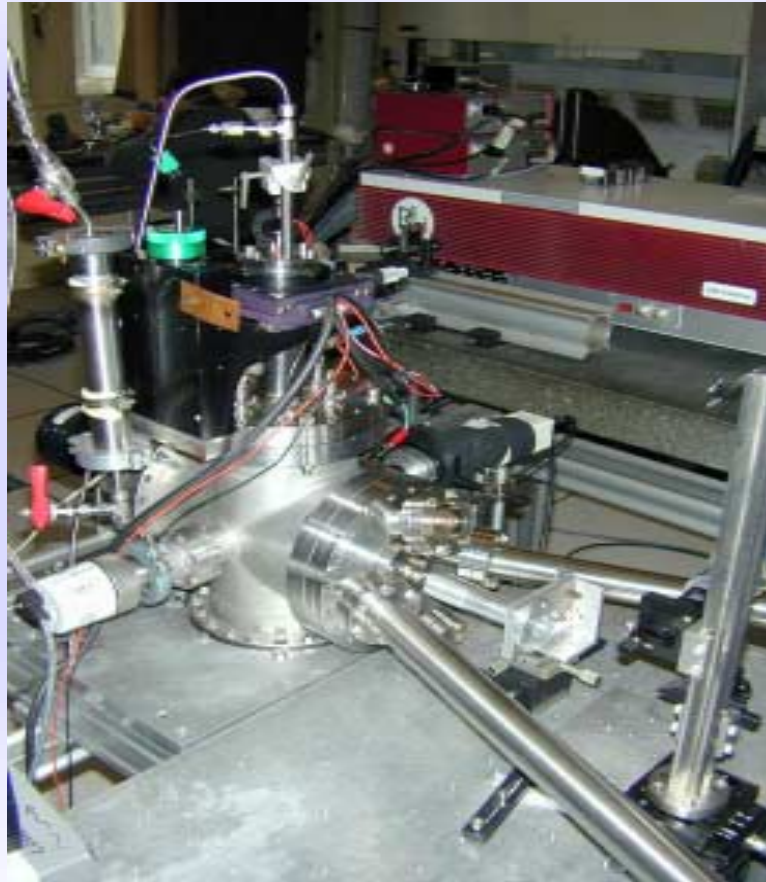
# Plasma laser source for EUV lithography

- Plasma excitation : laser ns (e.g. Nd :YAG)
- Target : Clusters jet

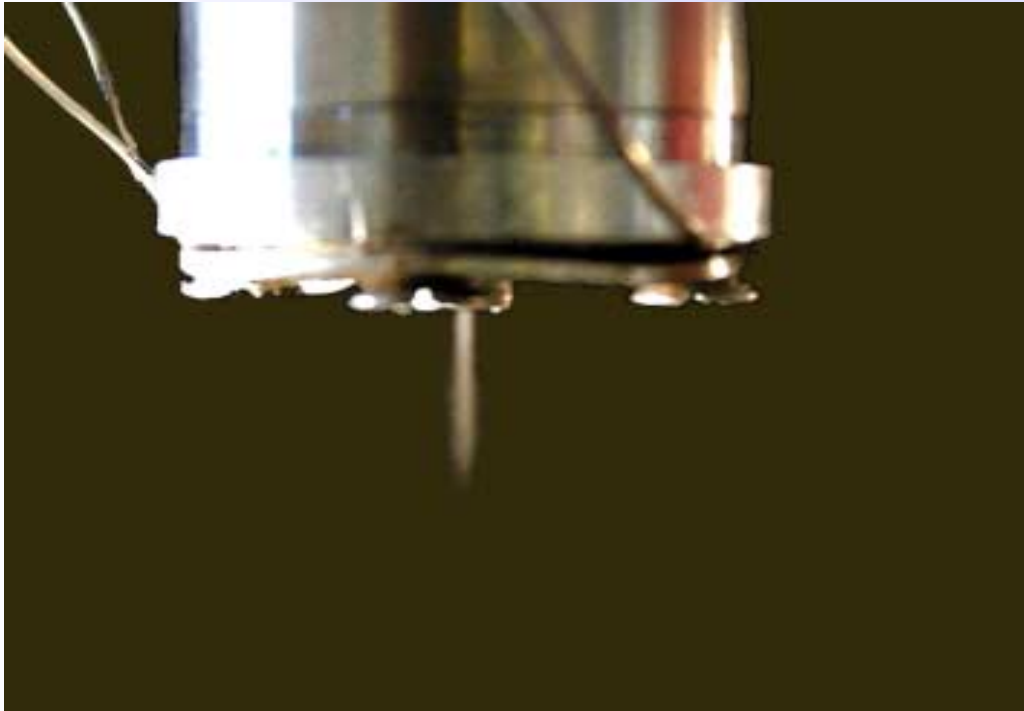


- cw target (high repetition rate)
- Low debris level
- Efficient laser-target Coupling (~ 100%)
- Compact and modular design
- Relatively simple technical solution

# Low rep rate EUV source set-up

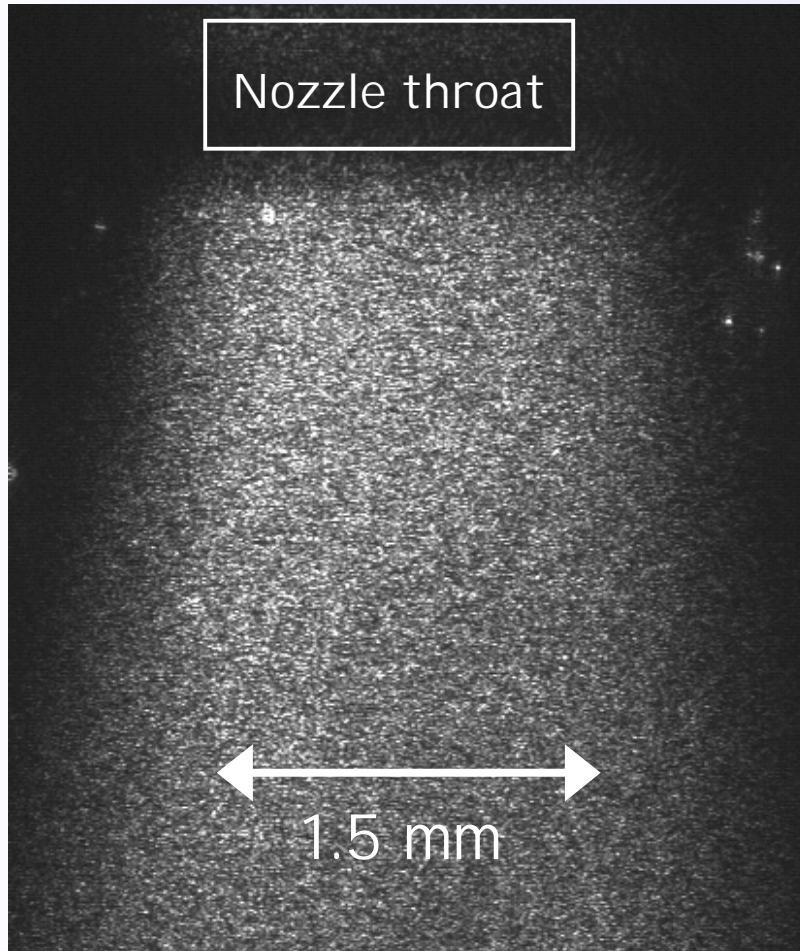


# Jet target design



Directive jet target :  
(~ 5° opening angle)  
⇒ no re-absorption  
in jet corona  
⇒ interaction zone  
@ 1-5mm from nozzle

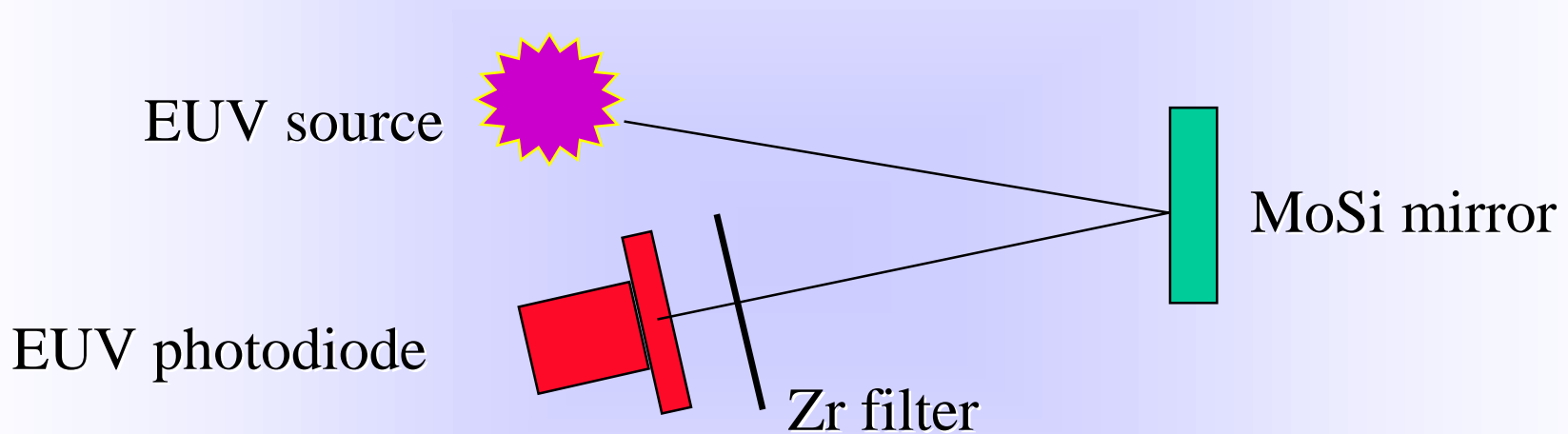
# Zoom on the Saclay jet target



- Low cost target material (i.e. no recycling)
- Jet density =  $10^{20}$  atoms/cm<sup>3</sup> @ interaction zone (cf. less than critical density @  $\lambda = 1\mu\text{m}$ )
- Particle size  $1\mu\text{m} \dots 100\mu\text{m}$
- Target flow speed  $\sim 100\text{m/s}$   $\Rightarrow$  laser rep. rates of 10kHz are possible

# Preliminary photonflux and conversion efficiency of the Saclay source

Method of measure : « multilayer monochromator »



A - mirrors (B. Vidal, Marseille - PREUVE)  
calibration by CEA/DAM @ LURE, Orsay

B - photodiodes (UDT UVX-100)  
calibration by PTB @ Bessy 2, Berlin

# EUV photon counting device



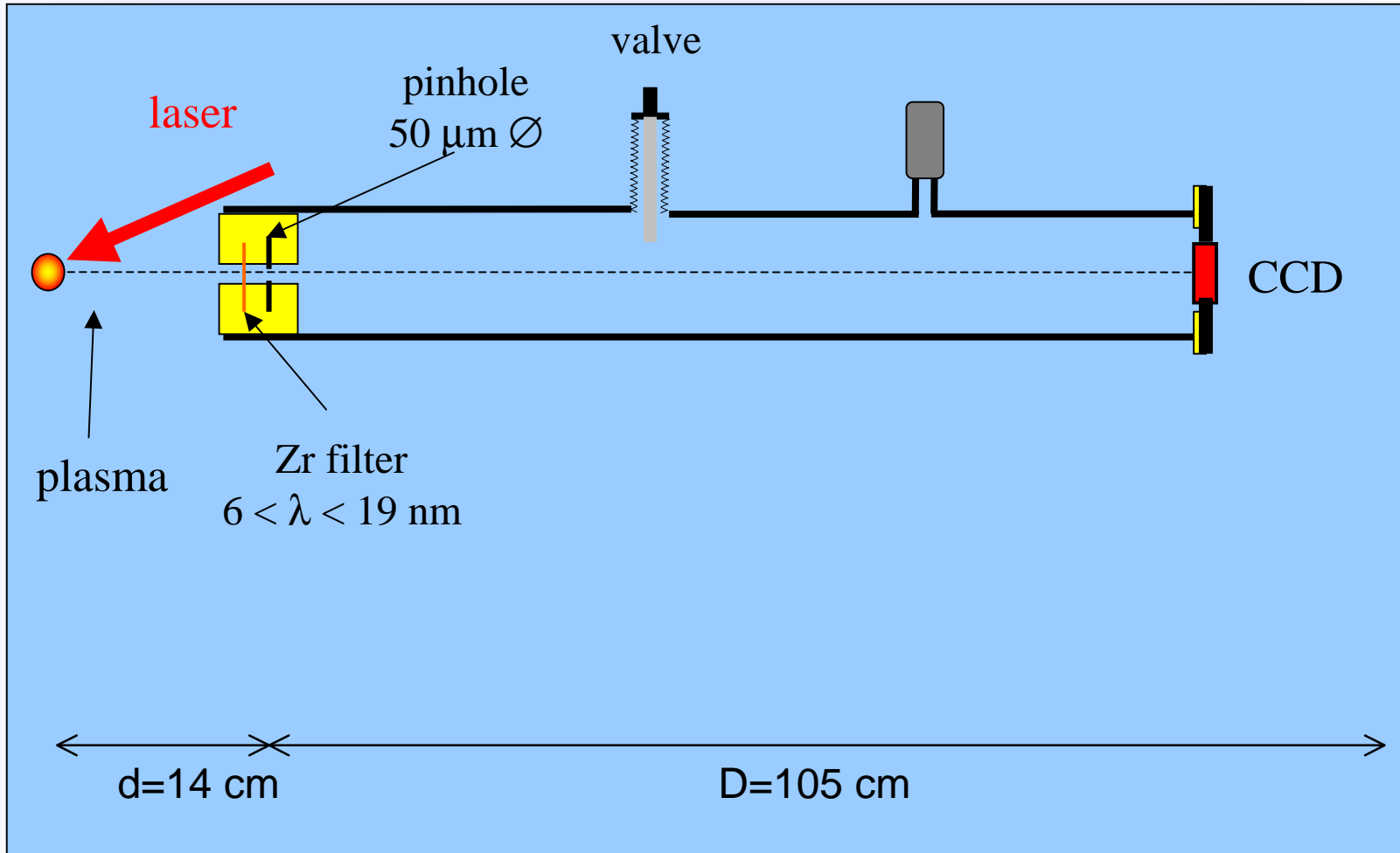
- Multilayer monochromator
- Zr filters
- calibrated EUV diodes

# Transmission grating Spectrograph\*



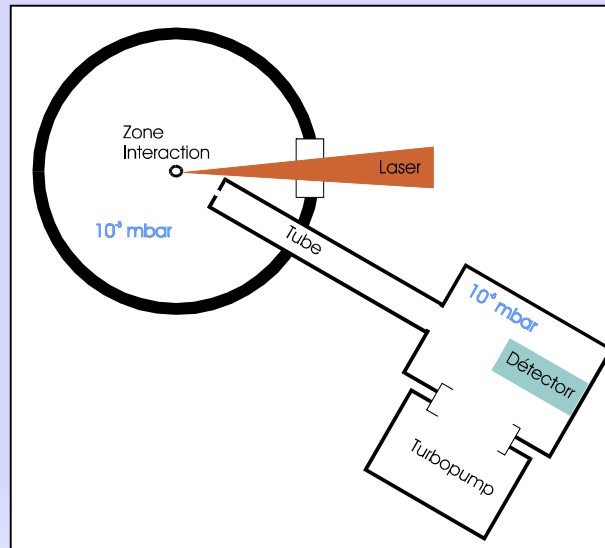
\* courtesy of : Prof. Schmahl, Institut für Röntgenphysik

# Pinhole imaging



# Debris analysis and impact on collector optics

« Plunging pinhole » time-of-flight mass-spectrometry for direct debris ion measurements (energy + charge)



Empiric studies of MoSi multilayer mirror lifetimes

Optimisation of an anti-debris device\*

(patent for anti-debris device in preparation)

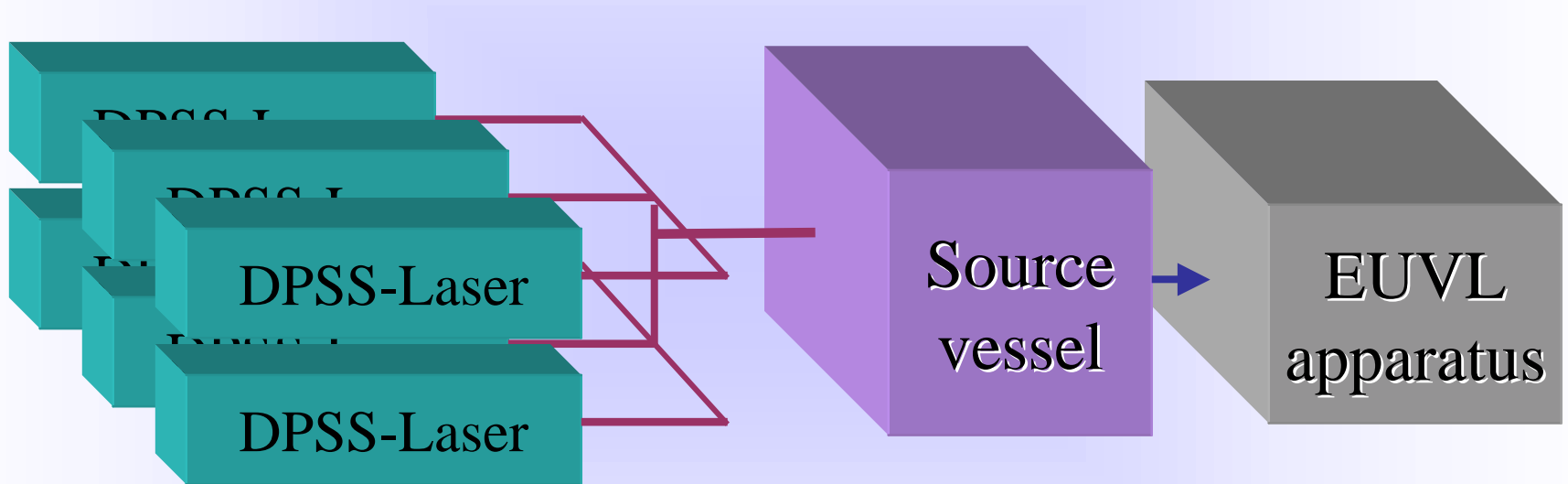
# Sketch of the Saclay cw EUV source set-up (PREUVE)



# DPSS pump laser design

- home-made (TCL) cw diode pumped Nd:YAG
- one power unity : pure oscillator design (no amps)
- n identical power units for EUV source pumping
- high repetition rates achievable ( $\geq 10\text{kHz}$ )
- spatial "multi-beam" multiplexing

# Schematic presentation of the EUV source apparatus



Evolving pump power management

# Conclusions

